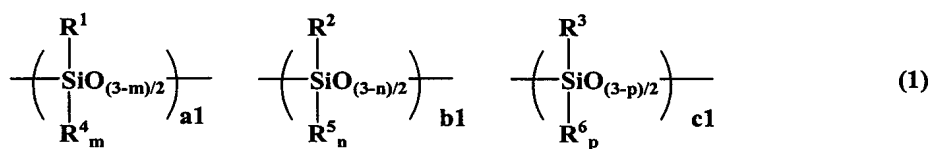


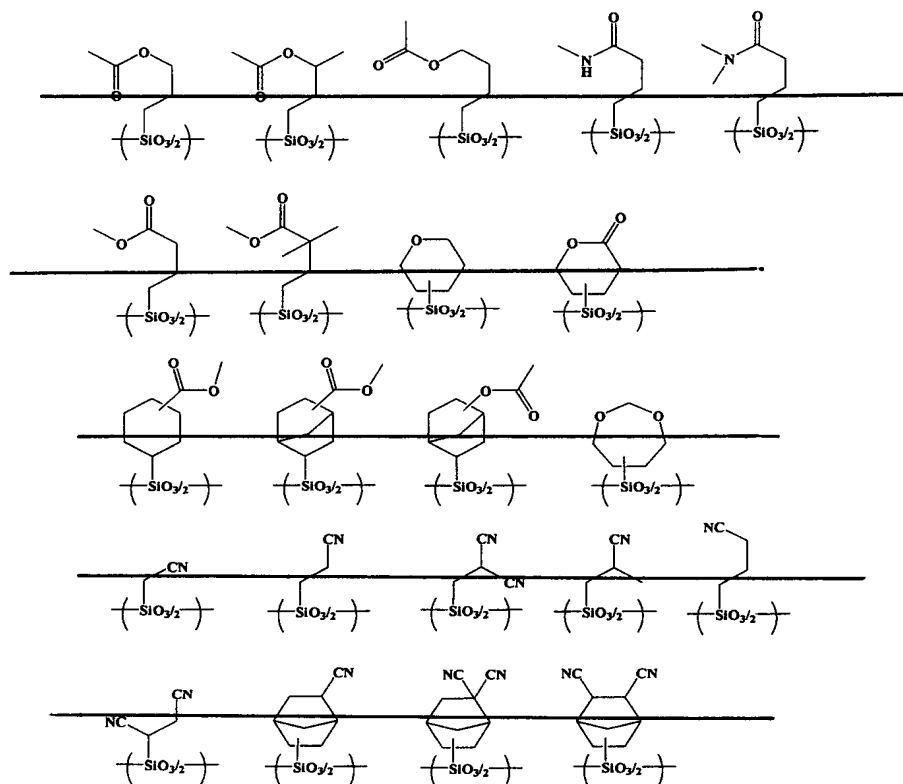
Amendments to the Claims:

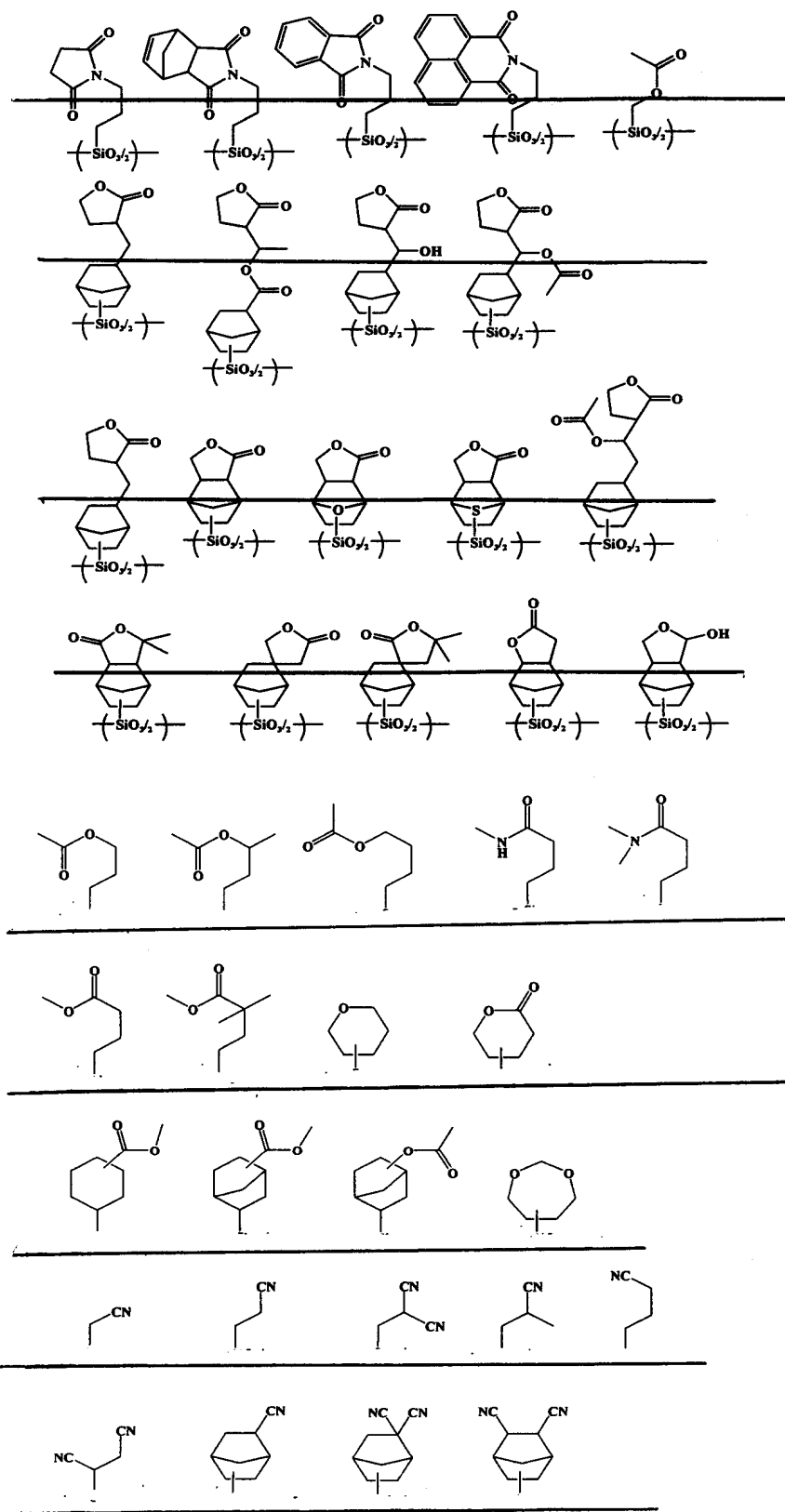
The following listing of claims will replace all prior versions, and listings, of claims in the application:

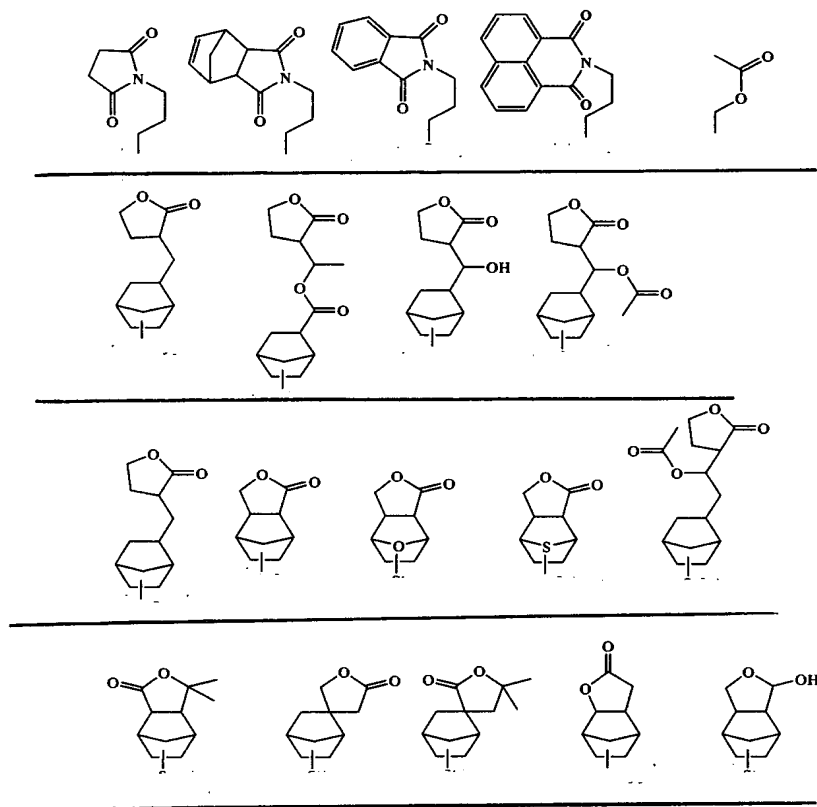
1. (Currently Amended) An anti-reflection film material used in lithography which is an anti-reflection film material used in lithography and contains at least a polymer compound having repeating units for copolymerization represented by the following general formula (1):



wherein R^1 is a monovalent organic group having a crosslink group, R^2 is a monovalent organic group having a light-absorption group, and R^3 is a monovalent organic group selected from the group consisting of:

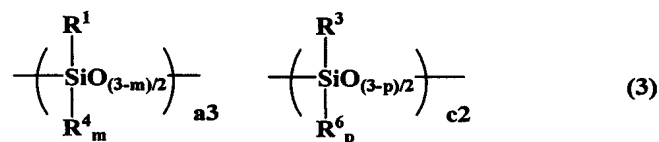
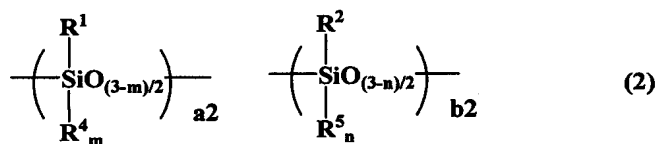




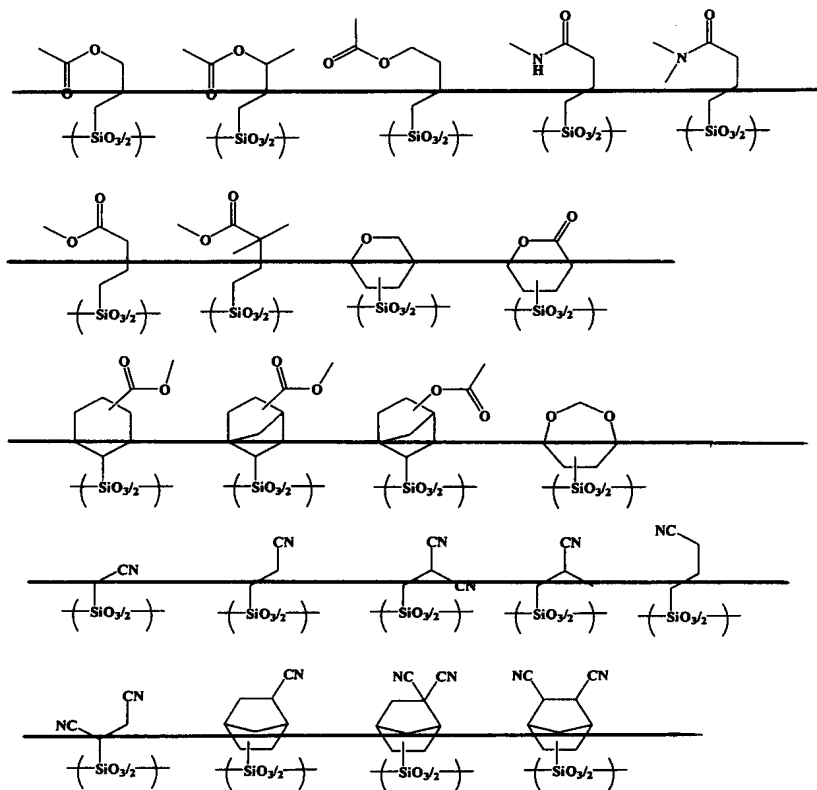


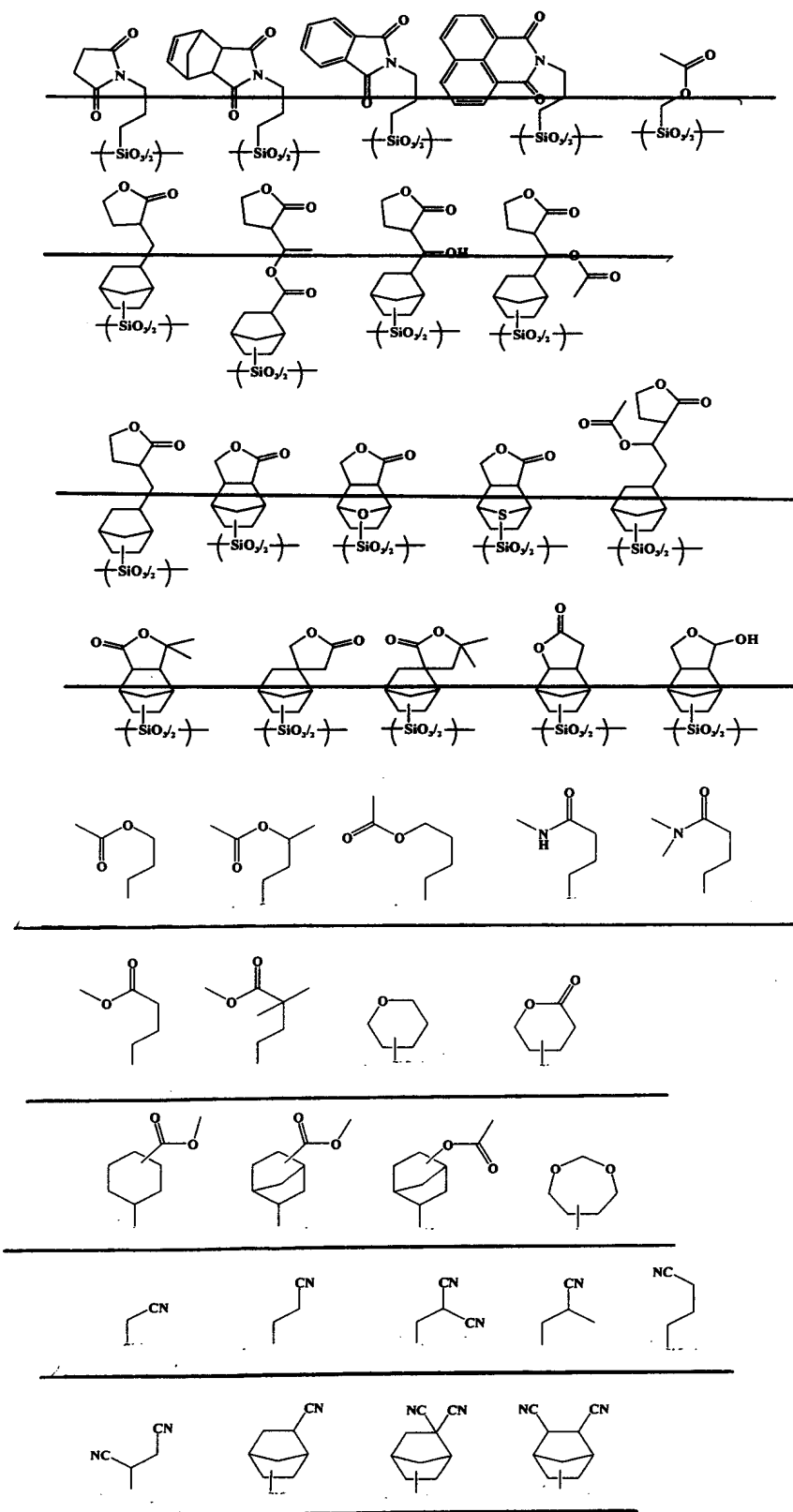
; a_1 , b_1 and c_1 are $0 < a_1 < 1$, $0 < b_1 < 1$, $0 < c_1 < 1$, and $0.5 \leq a_1 + b_1 + c_1 \leq 1$; each of R^4 , R^5 and R^6 is a hydrogen atom, a hydroxy group, an alkyl group having 1-6 carbon atoms, an aryl group having 6-10 carbon atoms, or a fluorinated alkyl group having 1-6 carbon atoms; and each of m , n and p is 0 or 1.

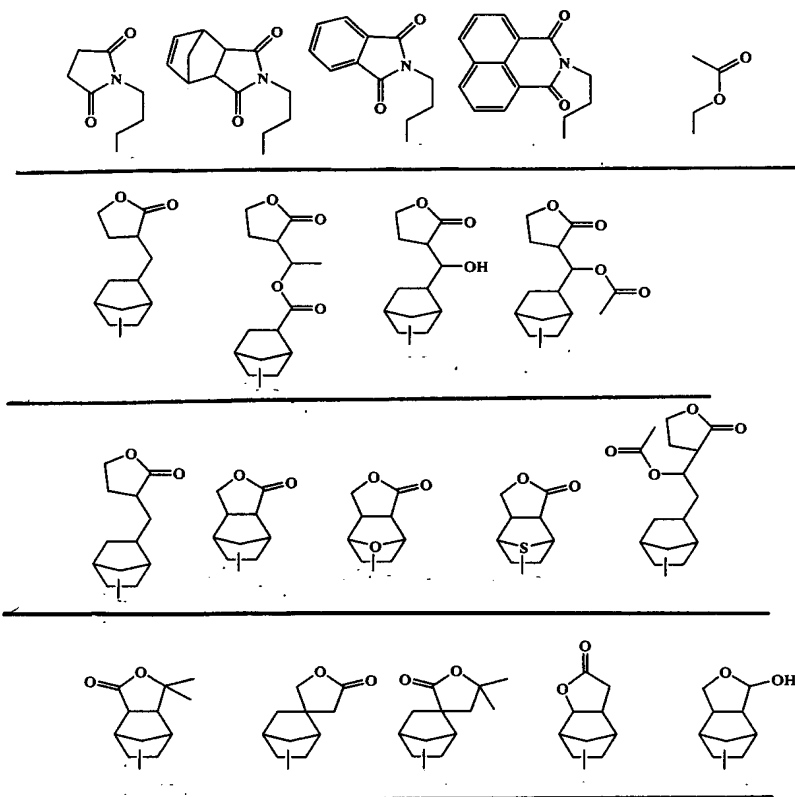
2. (Currently Amended) An anti-reflection film material used in lithography which is an anti-reflection film material used in lithography and contains at least a polymer compound having repeating units for copolymerization represented by the following general formula (2) and a polymer compound having repeating units for copolymerization represented by the following general formula (3):



wherein R^1 is a monovalent organic group having a crosslink group, R^2 is a monovalent organic group having a light-absorption group, and R^3 is a monovalent organic group selected from the group consisting of:







; each of R^4 , R^5 , and R^6 is a hydrogen atom, a hydroxy group, an alkyl group having 1-6 carbon atoms, an aryl group having 6-10 carbon atoms, or a fluorinated alkyl group having 1-6 carbon atoms; each of m , n and p is 0 or 1; a_2 and b_2 are $0 < a_2 < 1$, $0 < b_2 < 1$, and $0.5 \leq a_2 + b_2 \leq 1$; and a_3 and c_2 are $0 < a_3 < 1$, $0 < c_2 < 1$, and $0.5 \leq a_3 + c_2 \leq 1$.

3. (Original) The anti-reflection film material according to Claim 1 which further contains an organic solvent and/or an acid generating agent.

4. (Original) The anti-reflection film material according to Claim 2 which further contains an organic solvent and/or an acid generating agent.

5. (Original) The anti-reflection film material according to Claim 1 which further contains a crosslinking agent.

6. (Original) The anti-reflection film material according to Claim 2 which further contains a crosslinking agent.
7. (Original) The anti-reflection film material according to Claim 1 wherein the light-absorption group in the repeating unit of the polymer compound contained in the anti-reflection film material is an aromatic group or a group having a Si-Si bond.
8. (Original) The anti-reflection film material according to Claim 2 wherein the light-absorption group in the repeating unit of the polymer compound contained in the anti-reflection film material is an aromatic group or a group having a Si-Si bond.
9. (Original) A substrate which has at least an anti-reflection film obtained by baking the anti-reflection film material according to Claim 1 on the substrate.
10. (Original) A substrate which has at least an anti-reflection film obtained by baking the anti-reflection film material according to Claim 2 on the substrate.
11. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, and etching the anti-reflection film and the substrate with using as a mask the photoresist film on which the resist pattern is formed to form a pattern on the substrate.
12. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according

to Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, and etching the anti-reflection film and the substrate with using as a mask the photoresist film on which the resist pattern is formed to form a pattern on the substrate.

13. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film with using as a mask the photoresist film on which the resist pattern is formed, and etching the substrate with using as a mask the anti-reflection film on which the pattern is formed, to form a pattern on the substrate.

14. (Original) A method for forming a pattern on a substrate by lithography comprising at least applying to the substrate an anti-reflection film material according to Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying to the anti-reflection film a photoresist film material and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the

photoresist film, etching the anti-reflection film with using as a mask the photoresist film on which the resist pattern is formed, and etching the substrate with using as a mask the anti-reflection film on which the pattern is formed, to form a pattern on the substrate.

15. (Original) A method for forming a pattern on a substrate by lithography comprising at least, forming an organic film on the substrate, applying to the organic film the anti-reflection film material of Claim 1 and baking the anti-reflection film material to form an anti-reflection film, applying a photoresist film material to the anti-reflection film and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film using as a mask the photoresist film on which the resist pattern is formed, etching the organic film using as a mask the anti-reflection film on which the pattern is formed, and etching the substrate to form a pattern on the substrate.

16. (Original) A method for forming a pattern on a substrate by lithography comprising at least, forming an organic film on the substrate, applying to the organic film the anti-reflection film material of Claim 2 and baking the anti-reflection film material to form an anti-reflection film, applying a photoresist film material to the anti-reflection film and pre-baking the photoresist film material to form a photoresist film, exposing a pattern circuit range of the photoresist film, developing with a developer to form a resist pattern on the photoresist film, etching the anti-reflection film using as a mask the photoresist film on which the resist pattern is formed, etching

the organic film using as a mask the anti-reflection film on which the pattern is formed, and etching the substrate to form a pattern on the substrate.